PAN	ĴΤ
	SEMI CONDUCTOR

60V N-Channel Enhancement Mode MOSFET

Voltage

60 V Current

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@8A < 50m\Omega$
- $R_{DS(ON)}$, V_{GS} @4.5V, I_D @4A<60m Ω
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

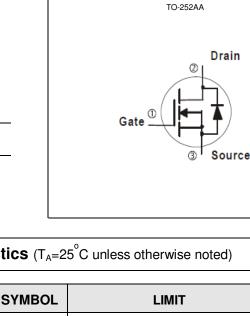
- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0104 ounces, 0.297grams

Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

16 A

PARAMET	ER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V
Continuous Drain Current	T _C =25°C	I	16	
	T _C =100°C	I _D	10	А
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	64	
Power Dissipation	T _C =25°C	Po	27	14/
	T _C =100°C		10.8	W
Continuous Drain Current	T _A =25°C	I _D	4.4	А
	T _A =70°C		3.5	А
Power Dissipation	T _A =25°C	D	2.0	14/
Power Dissipation	T _A =70°C	Po	1.3	- W
Single Pulse Avalanche Energy	(Note 6)	E _{AS}	11	mJ
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R _{θJC}	4.6	°0.00
	Junction to Ambient	$R_{\theta JA}$	62.5	°C/W

Limited only By Maximum Junction Temperature





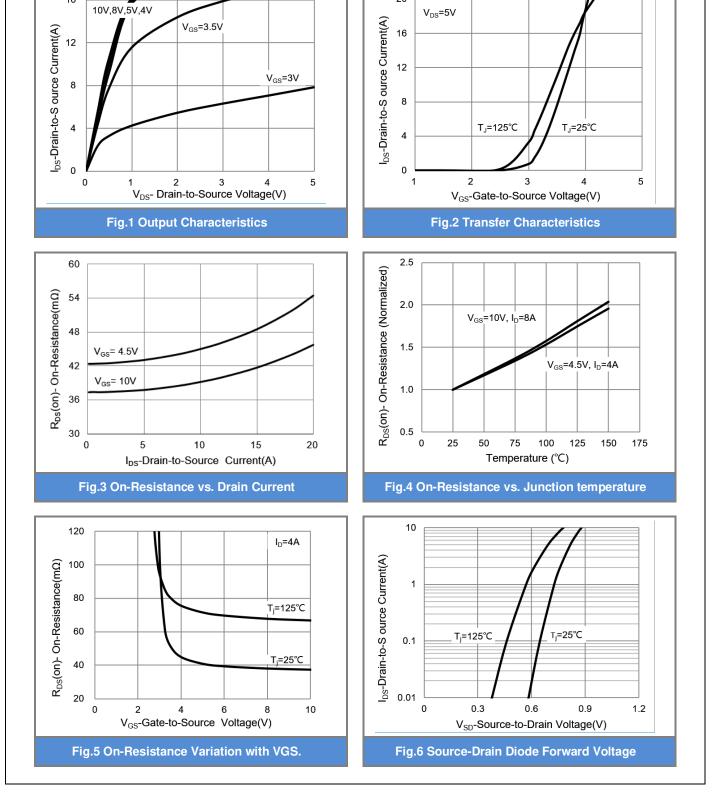
Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	1.0	1.77	2.5	V
Ducia Course On Otata Decistance		V_{GS} =10V,I _D =8A	-	37	50	mΩ
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =4.5V,I _D =4A	-	42	60	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V_{DS} =30V, I _D =4A, V_{GS} =10V ^(Note 1,2)	-	14	-	nC
Gate-Source Charge	Q _{gs}		-	2.9	-	
Gate-Drain Charge	Q _{gd}		-	2.3	-	
Input Capacitance	Ciss		-	815	-	
Output Capacitance	Coss	V _{DS} =15V, V _{GS} =0V, f=1.0MHZ	-	379	-	pF
Reverse Transfer Capacitance	Crss		-	110	-	
Turn-On Delay Time	td _(on)	V _{DD} =30V, I _D =1A, V _{GS} =10V, R _G =3.3Ω	-	3.9	-	
Turn-On Rise Time	tr		-	13	-	ns
Turn-Off Delay Time	td _(off)		-	23	-	
Turn-Off Fall Time	t _f		-	6.7	-	
Drain-Source Diode						
Maximum Continuous Drain-Source				-	16	A
Diode Forward Current	I _S		-			
Diode Forward Voltage	V _{SD}	I _S =1A,V _{GS} =0V	-	0.73	1.0	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. Reua is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, $I_{AS}{=}15A,\,V_{DD}{=}25V,\,V_{GS}{=}10V$
- 7. Guaranteed by design, not subject to production testing.

May 25,2016-REV.00



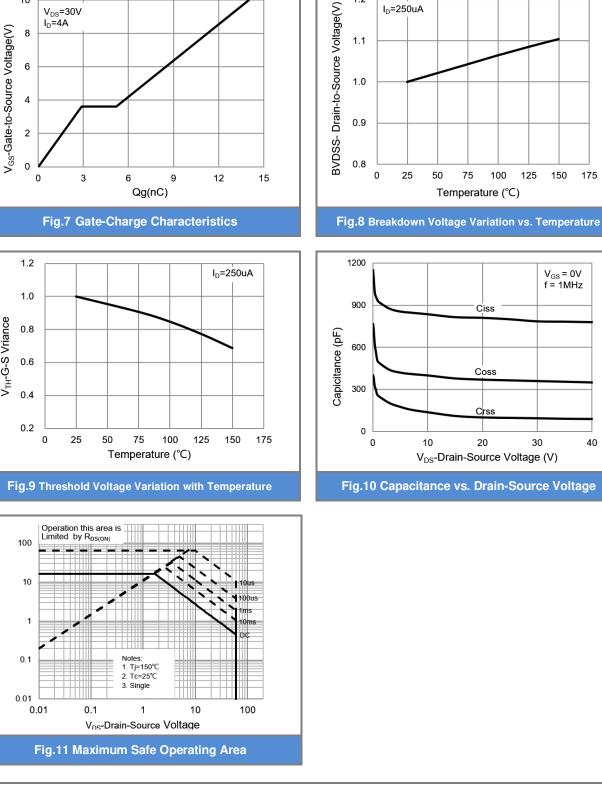
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PJD16N06A

TYPICAL CHARACTERISTIC CURVES

16

May 25,2016-REV.00



1.2

I_D=250uA

PJD16N06A

V_{DS}=30V I_D=4A

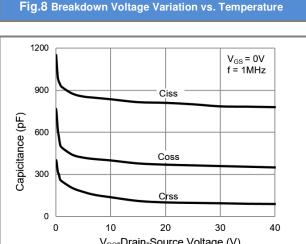
TYPICAL CHARACTERISTIC CURVES

PANJ SEMI CONDUCTOR

10

8

V_{TH}-G-S Vriance



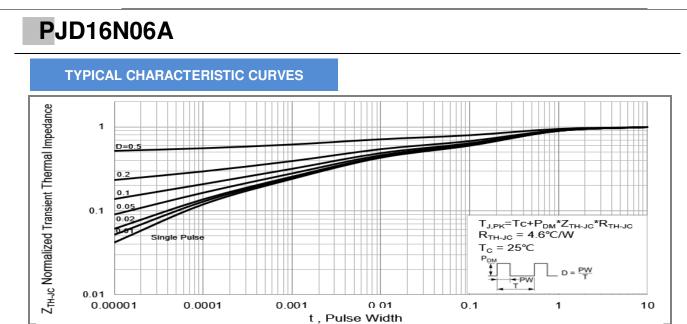


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

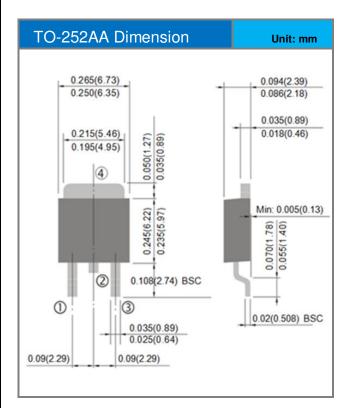








Packaging Information



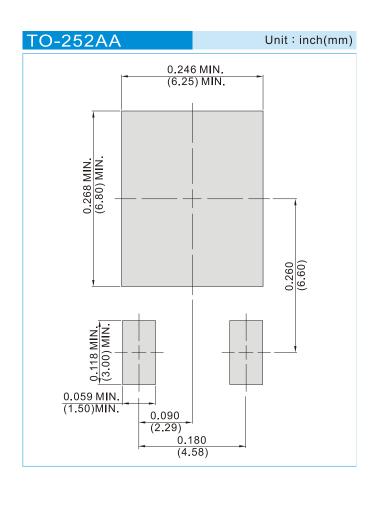




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD16N06A_L2_00001	TO-252AA	3,000pcs / 13" reel	D16N06A	Halogen free

MOUNTING PAD LAYOUT





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PJD16N06A

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